

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	((("3,467,906") or ("3,828,231") or ("4,794,346") or ("5,305,412") or ("5,436,759") or ("5,604,628") or ("5,805,322"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/27 11:25
L2	423	communic\$5 and fiber and VCSEL and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:50
L3	1	2 and (trap\$4 near2 like near2 defect) and (lattice near3 mismatch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:17
L4	7	2 and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:35
L5	60	2 and (defect) and (lattice near3 mismatch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:18
L6	7	4 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:18
L7	9	("5034783" "5181086" "5404027" "5538918" "5617446" "5867516" "5991321" "6399970").PN. OR ("6647041").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/07/27 12:23
L8	39	("20020001112" "20040012845" "20040017604" "3467906" "3828231" "4794346" "5299054" "5305412" "5436759" "5604628" "5654822" "5673141" "5748653" "5754571" "5771320" "5778132" "5805322" "5949807" "5960024" "5999293" "6044100" "6061156" "6115517" "6128115" "6215583" "6243407" "6317531" "6333799" "6335992" "6347104" "6445495" "6462865" "6512629" "6522462" "6577654" "6647041" "6707600" "6714344").PN. OR ("6909536").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/07/27 12:32
L9	1	communic\$5 and fiber and VCSEL and ((dop\$4 near3 (layer or type or medium or film)) same (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:38
L10	1	9 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:39

L11	4	VCSEL and ((dop\$4 near3 (layer or type or medium or film)) same (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:48
L12	2	11 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:06
L15	3	fiber and VCSEL and ((dop\$4 near3 (layer or type or medium or film)) same (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:40
L16	1	15 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:39
L18	7	communic\$5 and fiber and Laser and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:03
L20	2	laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:51
L21	7	18 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 12:51
L22	7	communic\$5 and fiber and Laser and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and clad\$4 and confinement	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:04
L23	17	Laser and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and clad\$4 and confinement	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:10
L24	1	23 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:11
L25	15	Laser and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:13

L26	297	Laser and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and clad\$4 and confinement	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:29
L27	3	Laser and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4) and (trap\$4 near2 defect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:26
L28	1	27 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:11
L29	2	communic\$5 and fiber and VCSEL and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:13
L30	15	Laser and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material)) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 13:14
L31	1	(VCSEL OR VLSOA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near4 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4) and (trap\$4 near2 defect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:28
L32	5	(VCSEL OR VLSOA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near4 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4) and (confinement) and (trap\$4 near2 defect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:28
L33	1	(VCSEL OR VLSOA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near4 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4) and (trap\$4 near3 defect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:28
L34	1	(VCSEL OR VLSOA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near4 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (clad\$4 near4 dop\$4) and (confinement near4 dop\$4) and (trap\$4 near4 defect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:28
L35	6	(VCSEL OR VLSOA OR Laser) and (dop\$4 near3 (layer or type or medium or film)) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and clad\$4 and confinement and (trap\$4 near4 defect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:31
L36	6	(VCSEL OR VLSOA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and clad\$4 and confinement and (trap\$4 near4 defect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:31

L37	15	(VCSEL OR VLSEA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (trap\$4 near4 defect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:31
L38	14	(VCSEL OR VLSEA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror or reflect\$4) and (lattice near3 mismatch\$3) and (trap\$4 near4 defect\$3) and (active or gain) and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:44
L39	430	(VCSEL OR VLSEA OR Laser) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:42
L40	358	interface and 39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:42
L41	13	40 and bulk near3 dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:43
L42	13	40 and (bulk\$4 near3 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:44
L44	2	42 and 38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 15:45
S1	3	"6647041"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/07/27 11:03